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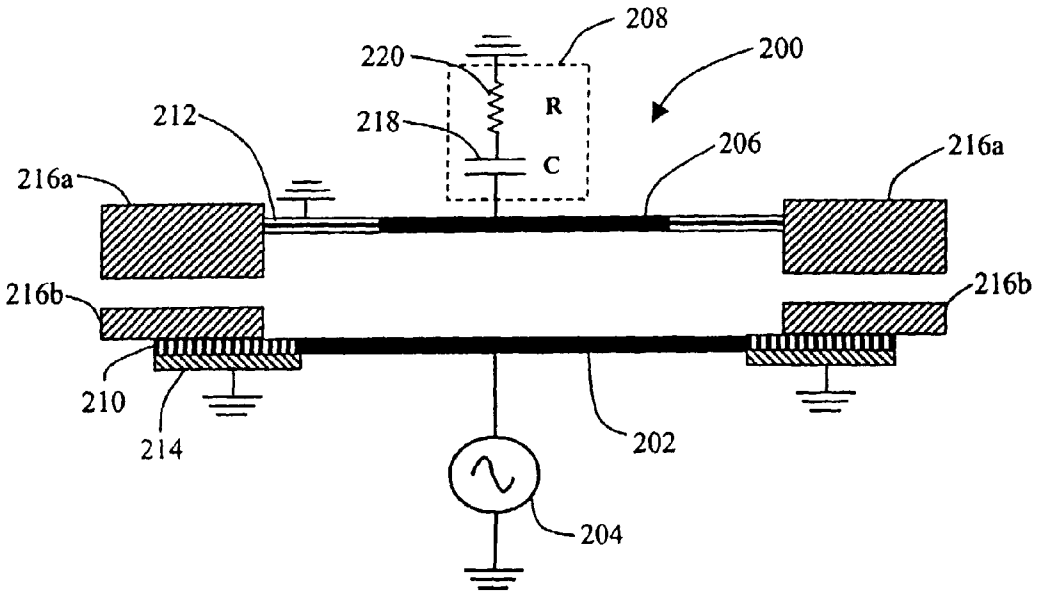
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(54) Title: A SYSTEM AND METHOD FOR CONTROLLING PLASMA WITH AN ADJUSTABLE COUPLING TO GROUND CIRCUIT




(57) Abstract: A system and method for controlling plasma. The system includes a semiconductor chamber comprising a powered electrode, another electrode, and an adjustable coupling to ground circuit. The powered electrode is configured to receive a wafer or substrate. There is at least one grounded electrode configured to generate an electrical connection with the powered electrode. At least one of the grounded electrodes is electrically coupled to the adjustable coupling to ground circuit. The adjustable coupling to ground circuit is configured to modify the impedance of the grounded electrode. The ion energy of the plasma is controlled by the adjustable coupling to ground circuit.

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